



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-92L Plastic-Encapsulate Transistors

2SB562 TRANSISTOR (PNP)

FEATURES

- Low frequency power amplifier.
- Complementary pair with 2SD468

TO-92L

1. EMITTER
2. COLLECTOR
3. BASE



1 2 3

MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-25	V
V_{CEO}	Collector-Emitter Voltage	-20	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-1	A
P_C	Collector power dissipation	0.9	W
T_J	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55-150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-10\mu\text{A}, I_E=0$	-25			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1\text{mA}, I_B=0$	-20			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-10\mu\text{A}, I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-20\text{V}, I_E=0$			-1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-4\text{V}, I_C=0$			-1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=-2\text{V}, I_C=-0.5\text{A}$	85		240	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-0.8\text{A}, I_B=-0.08\text{A}$			-0.5	V
Base-emitter voltage	V_{BE}	$V_{CE}=-2\text{V}, I_C=-0.5\text{A}$			-1	V
Transition frequency	f_T	$V_{CE}=-2\text{V}, I_C=-0.5\text{A}$		350		MHz
Collector output capacitance	C_{ob}	$V_{CB}=-10\text{V}, I_E=0, f=1\text{MHz}$		38		pF

CLASSIFICATION OF $h_{FE(1)}$

Rank	B	C
Range	85-170	120-240

Typical Characteristics

2SB562



